



## N-Channel 30-V (D-S) MOSFET

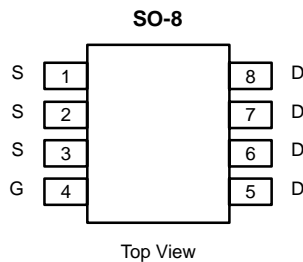
PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
30	0.0045 @ $V_{GS} = 10$ V	20
	0.0055 @ $V_{GS} = 4.5$ V	17

### FEATURES

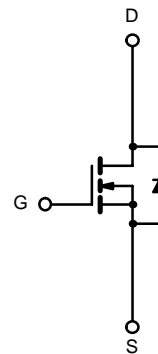
- TrenchFET® Power MOSFET
- Optimized for “Low Side” Synchronous Rectifier Operation
- 100%  $R_G$  Tested

### APPLICATIONS

- DC/DC Converters
- Synchronous Rectifiers



Ordering Information: Si4406DY  
Si4406DY-T1 (with Tape and Reel)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		$V_{DS}$	30		V
Gate-Source Voltage		$V_{GS}$	$\pm 20$		
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$T_A = 25^\circ\text{C}$	$I_D$	20	13	A
	$T_A = 70^\circ\text{C}$		15	10	
Pulsed Drain Current (10 $\mu\text{s}$ Pulse Width)		$I_{DM}$	60		
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	2.9	1.3	W
Maximum Power Dissipation <sup>a</sup>	$T_A = 25^\circ\text{C}$	$P_D$	3.5	1.6	
	$T_A = 70^\circ\text{C}$		2.2	1	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10$ sec	$R_{thJA}$	29	35	$^\circ\text{C/W}$
	Steady State		67	80	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	13	16	

Notes

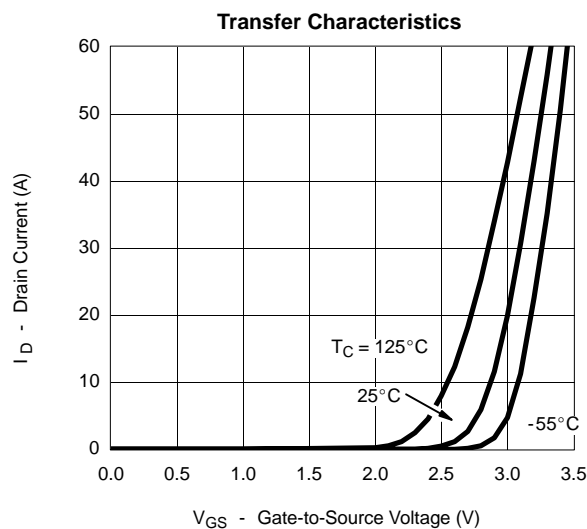
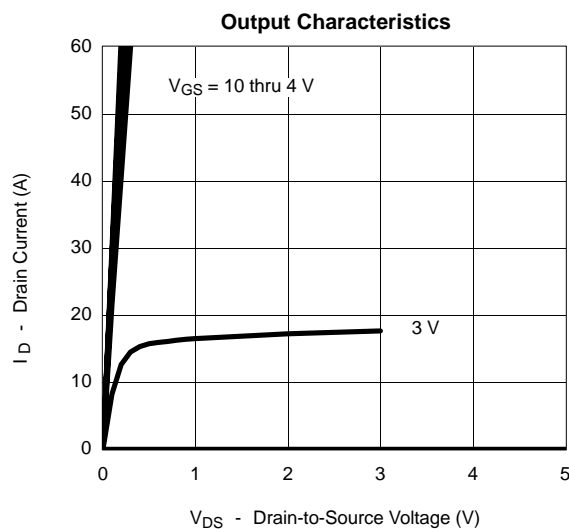
a. Surface Mounted on 1" x 1" FR4 Board.

**SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.0	1.95	3.0	V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	30			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.0035	0.0045	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 19 A		0.0043	0.0055	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		95		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 2.9 A, V <sub>GS</sub> = 0 V		0.72	1.1	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A		34	50	nC
Gate-Source Charge	Q <sub>gs</sub>			15		
Gate-Drain Charge	Q <sub>gd</sub>			10		
Gate Resistance	R <sub>G</sub>		0.5	1.3	2.2	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 15 Ω I <sub>D</sub> ≅ 1 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 6 Ω		21	35	ns
Rise Time	t <sub>r</sub>			15	25	
Turn-Off Delay Time	t <sub>d(off)</sub>			100	150	
Fall Time	t <sub>f</sub>			30	45	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.9 A, di/dt = 100 A/μs		50	80	

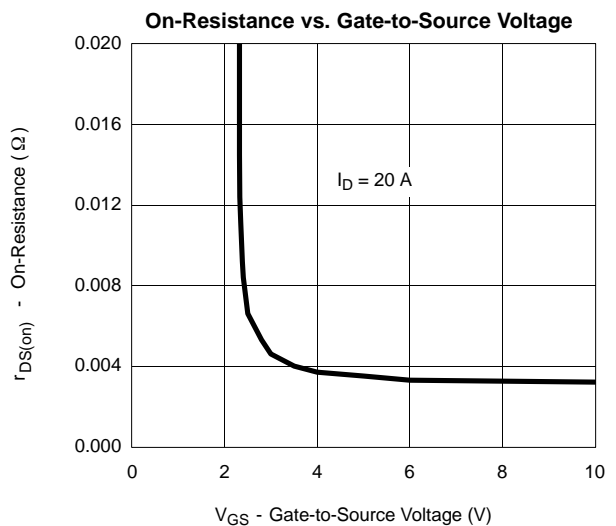
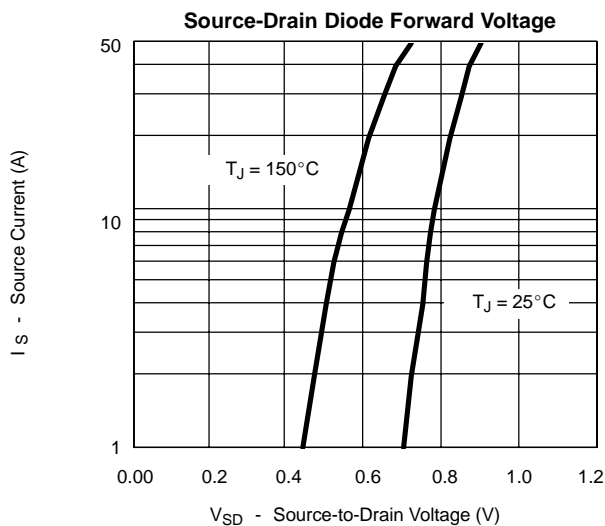
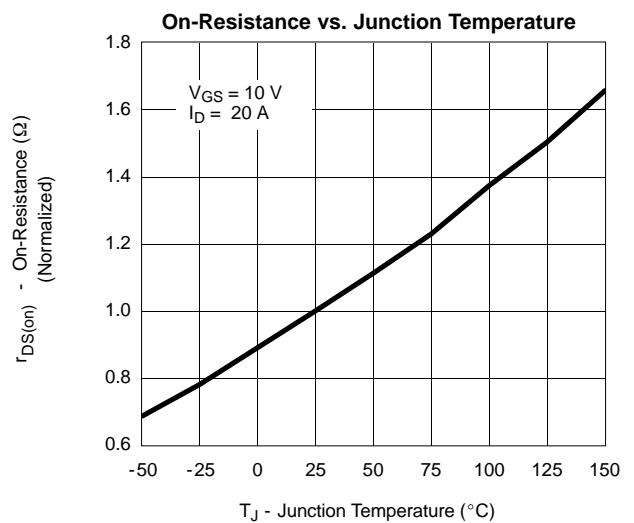
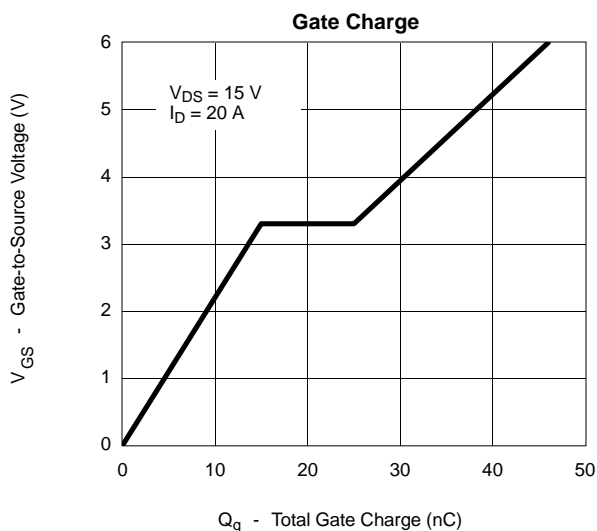
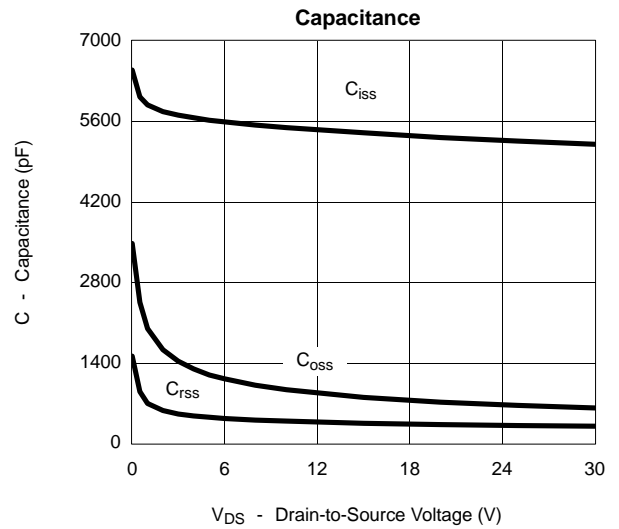
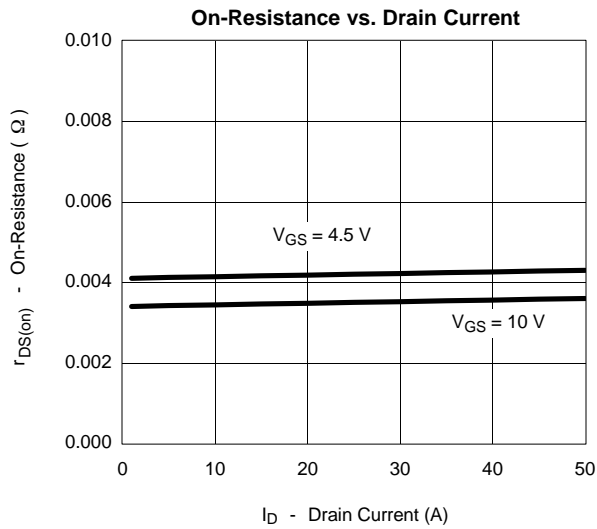
## Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.  
b. Guaranteed by design, not subject to production testing.

**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**



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